Unit in mm

TENTATIVE

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2 S C 5 3 2 2

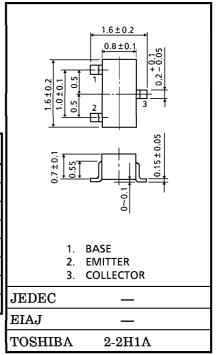
VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

• Low Noise Figure : NF = 1.4 dB (f = 2 GHz)

• High Gain : Ga = 10 dB (f = 2 GHz)

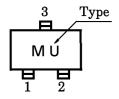
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	8	V
Collector-Emitter Voltage	v_{CEO}	5	V
Emitter-Base Voltage	$V_{ m EBO}$	1.5	V
Collector Current	$I_{\mathbf{C}}$	10	mA
Base Current	$I_{\mathbf{B}}$	5	mA
Collector Power Dissipation	PC	100	mW
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C



Weight: 2.4 mg

MARKING



MICROWAVE CHARACTERISTICS (Ta = 25°C)

	•	•				
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	$ m f_{T}$	$V_{CE} = 3 V, I_{C} = 7 mA$	9	_	_	GHz
Incontion (ioin	$ S_{21e} ^2$ (1)	$ m V_{CE}=3~V,~I_{C}=7~mA,~f=1~GHz$	12.5	15.5	_	dB
	$ S_{21e} ^2$ (2)	$V_{CE} = 3 V, I_{C} = 7 mA, f = 2 GHz$	7	10	_	
Noise Figure	NF (1)	$V_{CE} = 3 V, I_{C} = 3 mA, f = 1 GHz$		0.9	1.8	dB
	NF (2)	$V_{CE} = 3 V, I_{C} = 3 mA, f = 2 GHz$		1.4	2.2	ub

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{CB} = 8 V, I_{E} = 0$	—	_	1	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 1 V, I_{C} = 0$	-	_	1	μ A
DC Current Gain	$h_{ extbf{FE}}$	$V_{CE} = 3 \text{ V}, I_{C} = 7 \text{ mA}$	50	_	250	V
Output Capacitance	C_{ob}	$V_{CB} = 2.5 \text{ V}, I_{E} = 0,$	T -	0.4	_	pF
Reverse Transfer Capacitance	$\mathrm{C_{re}}$	f = 1 MHz (Note)	_	0.3	0.7	pF

(Note): C_{re} is measured by 3 terminal method with Capacitance bridge.

CAUTION

This device electrostatic sensitivity. Please handle with caution.

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